

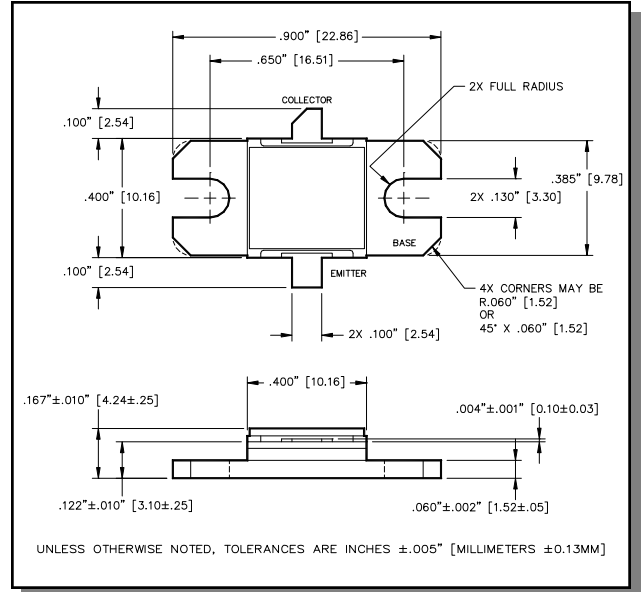
Radar Pulsed Power Transistor
5W, 2.7-3.1 GHz, 100µs Pulse, 10% Duty

M/A-COM Products
Released, 29 Jun 07

Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Outline Drawing



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I_C	0.7	A
Power Dissipation @ +25°C	P_{TOT}	50	W
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$		BV_{CES}	65	-	V
Collector-Emitter Leakage Current	$V_{CE} = 40\text{V}$		I_{CES}	-	1.0	mA
Thermal Resistance	$V_{CC} = 36\text{V}, P_{in} = 1.0\text{W}$	$F = 2.7, 2.9, 3.1\text{ GHz}$	$R_{TH(JC)}$	-	3.5	°C/W
Output Power	$V_{CC} = 36\text{V}, P_{in} = 1.0\text{W}$	$F = 2.7, 2.9, 3.1\text{ GHz}$	P_{OUT}	5.0	-	W
Power Gain	$V_{CC} = 36\text{V}, P_{in} = 1.0\text{W}$	$F = 2.7, 2.9, 3.1\text{ GHz}$	G_P	7.0	-	dB
Collector Efficiency	$V_{CC} = 36\text{V}, P_{in} = 1.0\text{W}$	$F = 2.7, 2.9, 3.1\text{ GHz}$	η_C	30	-	%
Input Return Loss	$V_{CC} = 36\text{V}, P_{in} = 1.0\text{W}$	$F = 2.7, 2.9, 3.1\text{ GHz}$	RL	-	-6	dB
Load Mismatch Tolerance	$V_{CC} = 36\text{V}, P_{in} = 1.0\text{W}$	$F = 2.7, 2.9, 3.1\text{ GHz}$	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 36\text{V}, P_{in} = 1.0\text{W}$	$F = 2.7, 2.9, 3.1\text{ GHz}$	VSWR-S	-	1.5:1	-

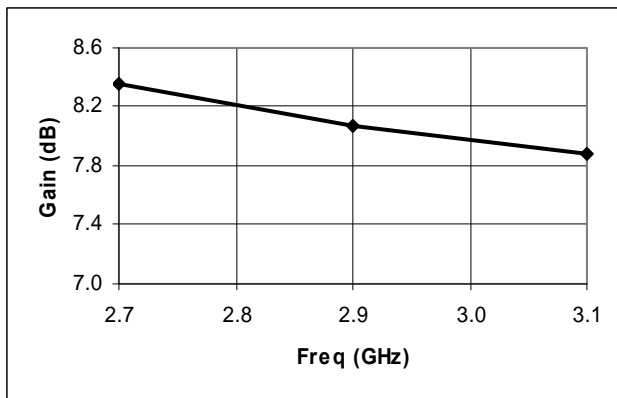
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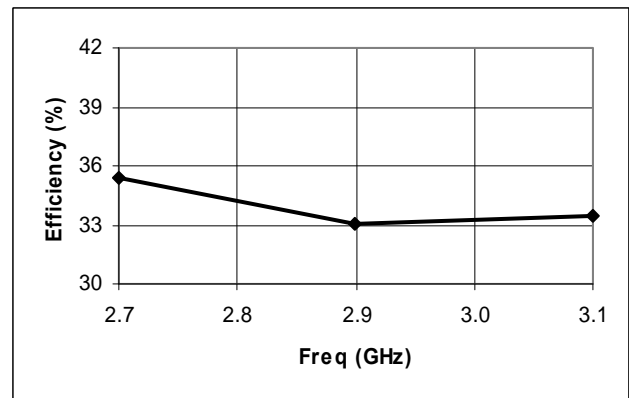
Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
2.7	1.0	5.6	7.47	0.48	32.6	-12.8	S	P
2.9	1.0	6.1	7.83	0.50	33.5	-16.7	S	P
3.1	1.0	6.2	7.89	0.51	33.8	-20.5	S	P

Gain vs. Frequency

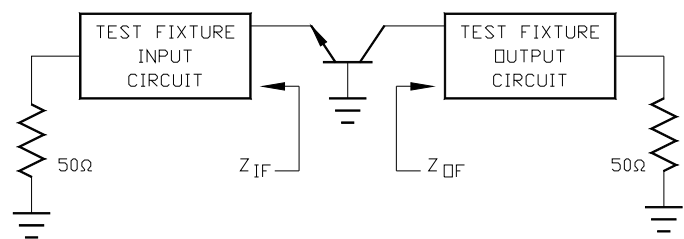


Collector Efficiency vs. Frequency



RF Test Fixture Impedance

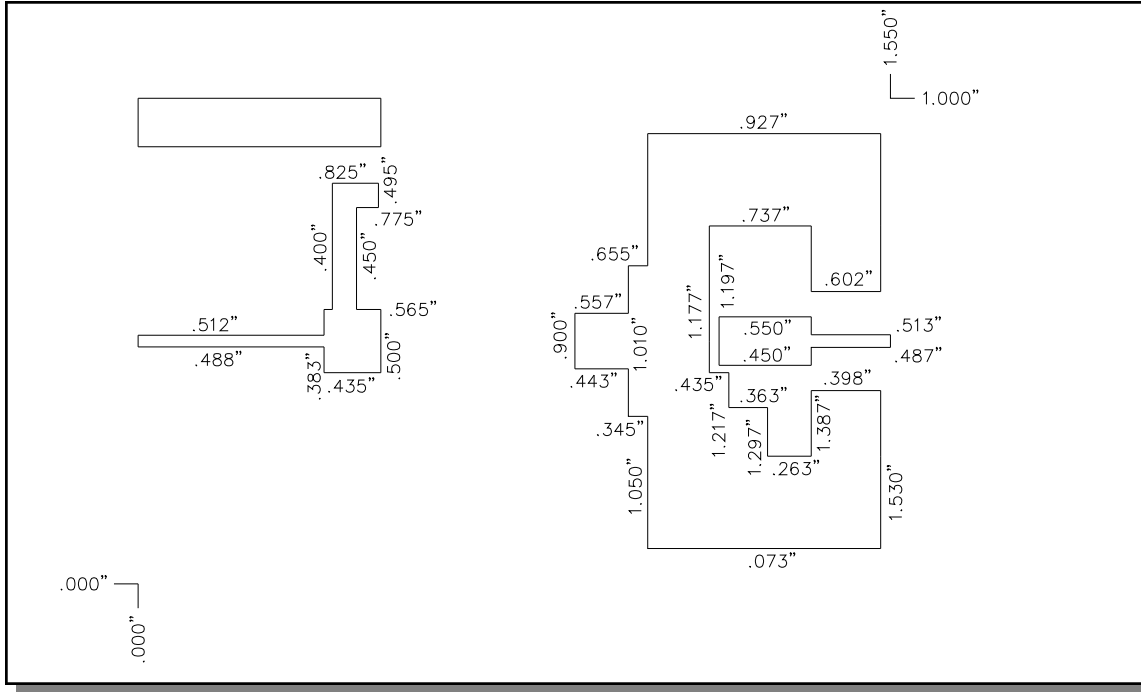
F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
2.7	40 - j12	25 + j3.5
2.9	35 - j16	16 + j2.4
3.1	30 - j18	12 + j4.0



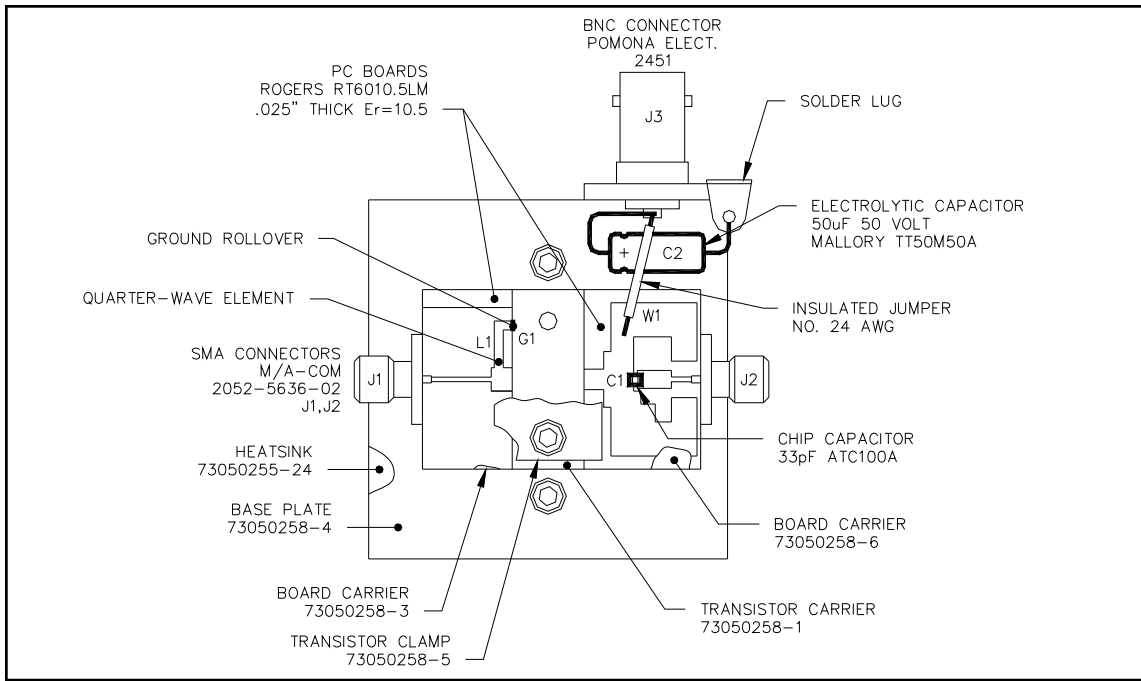
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Test Fixture Circuit Dimensions



Test Fixture Assembly



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